Low-power dual 2-input AND gate Rev. 7 — 18 January 2013

Product data sheet

#### **General description** 1.

The 74AUP2G08 provides the dual 2-input AND function.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire  $V_{CC}$  range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire  $V_{CC}$  range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using IOFF. The IOFF circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

#### **Features and benefits** 2.

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
  - JESD8-12 (0.8 V to 1.3 V)
  - JESD8-11 (0.9 V to 1.65 V)
  - JESD8-7 (1.2 V to 1.95 V)
  - JESD8-5 (1.8 V to 2.7 V)
  - JESD8-B (2.7 V to 3.6 V)
- ESD protection:
  - HBM JESD22-A114F Class 3A exceeds 5000 V
  - MM JESD22-A115-A exceeds 200 V
  - CDM JESD22-C101E exceeds 1 000 V
- Low static power consumption;  $I_{CC} = 0.9 \mu A$  (maximum)
- Latch-up performance exceeds 100 mA per JESD78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V<sub>CC</sub>
- I<sub>OFF</sub> circuitry provides partial power-down mode operation
- Multiple package options
- Specified from –40 °C to +85 °C and –40 °C to +125 °C



Low-power dual 2-input AND gate

### 3. Ordering information

Table 1. Ordering	g information			
Type number	Package			
	Temperature range	Name	Description	Version
74AUP2G08DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74AUP2G08GT	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 $\times$ 1.95 $\times$ 0.5 mm	SOT833-1
74AUP2G08GF	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.35 \times 1 \times 0.5$ mm	SOT1089
74AUP2G08GD	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body $3 \times 2 \times 0.5$ mm	SOT996-2
74AUP2G08GM	–40 °C to +125 °C	XQFN8	plastic, extremely thin quad flat package; no leads; 8 terminals; body $1.6 \times 1.6 \times 0.5$ mm	SOT902-2
74AUP2G08GN	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.2 \times 1.0 \times 0.35$ mm	SOT1116
74AUP2G08GS	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.35 \times 1.0 \times 0.35$ mm	SOT1203

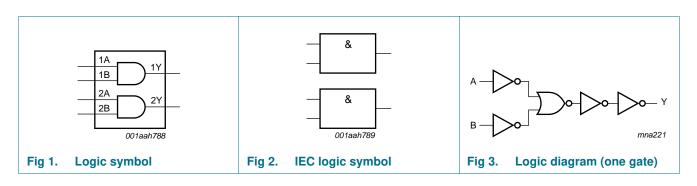
### 4. Marking

### Table 2.Marking codes

3	
Type number	Marking code <sup>[1]</sup>
74AUP2G08DC	p08
74AUP2G08GT	p08
74AUP2G08GF	pE
74AUP2G08GD	p08
74AUP2G08GM	p08
74AUP2G08GN	pE
74AUP2G08GS	pE

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

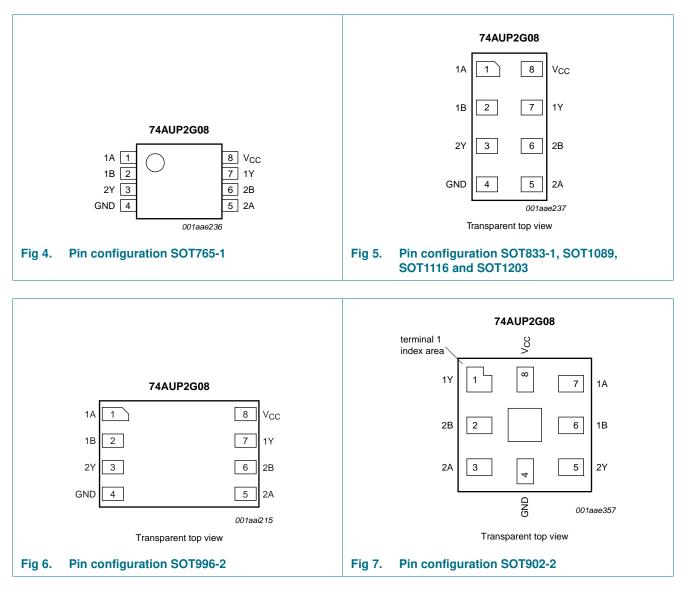
## 5. Functional diagram



Low-power dual 2-input AND gate

#### **Pinning information** 6.

### 6.1 Pinning



### 6.2 Pin description

Symbol	Pin	Pin		
	SOT765-1, SOT833-1, SOT1089, SOT996-2, SOT1116 and SOT1203	SOT902-2		
1A, 2A	1, 5	7, 3	data input	
1B, 2B	2, 6	6, 2	data input	
GND	4	4	ground (0 V)	
1Y, 2Y	7, 3	1, 5	data output	
V <sub>CC</sub>	8	8	supply voltage	
74AUP2G08	All information provided in t	his document is subject to legal discl	aimers. © NXP B.V. 2013. All rigi	hts reserved.
Product data	sheet Rev. 7 –	- 18 January 2013		3 of 21

### 7. Functional description

#### Table 4.Function table<sup>[1]</sup>

Input		Output
nA	nB	nY
L	L	L
L	Н	L
Н	L	L
Н	Н	Н

[1] H = HIGH voltage level;

L = LOW voltage level.

### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+4.6	V
I <sub>IK</sub>	input clamping current	V <sub>1</sub> < 0 V	-50	-	mA
VI	input voltage		<u>1</u> –0.5	+4.6	V
Ι <sub>ΟΚ</sub>	output clamping current	V <sub>O</sub> < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode	<u>1</u> –0.5	+4.6	V
I <sub>O</sub>	output current	$V_{O} = 0 V \text{ to } V_{CC}$	-	±20	mA
I <sub>CC</sub>	supply current		-	+50	mA
I <sub>GND</sub>	ground current		-50	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to \ +125 \ ^{\circ}C$	[2] _	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For VSSOP8 packages: above 110 °C the value of P<sub>tot</sub> derates linearly at 8.0 mW/K. For XSON8 and XQFN8 packages: above 118 °C the value of P<sub>tot</sub> derates linearly with 7.8 mW/K.

### 9. Recommended operating conditions

Table 6.	Operating conditions				
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode	0	V <sub>CC</sub>	V
		Power-down mode; $V_{CC} = 0 V$	0	3.6	V
T <sub>amb</sub>	ambient temperature		-40	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 0.8 V \text{ to } 3.6 V$	-	200	ns/V

## **10. Static characteristics**

#### Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T <sub>amb</sub> = 2	25 °C					
VIH	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.70 \times V_{CC}$	-	-	V
		$V_{CC} = 0.9 V$ to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		$V_{CC}$ = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	-	-	V
V <sub>IL</sub>	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.30 \times V_{CC}$	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		$V_{CC}$ = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
V <sub>OH</sub>	HIGH-level output voltage	$V_I = V_{IH} \text{ or } V_{IL}$				
		$I_O$ = –20 $\mu A;  V_{CC}$ = 0.8 V to 3.6 V	$V_{CC}-0.1$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.75 \times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.11	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.32	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	2.05	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.72	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.6	-	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_I = V_{IH} \text{ or } V_{IL}$				
		$I_O$ = 20 $\mu A;V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		$I_{O} = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.3\times V_{CC}$	V
		$I_{O} = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.31	V
		$I_{O} = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.31	V
		$I_{O} = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	V
		$I_{O} = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	V
I	input leakage current	$V_{\rm I}$ = GND to 3.6 V; $V_{\rm CC}$ = 0 V to 3.6 V	-	-	±0.1	μA
OFF	power-off leakage current	$V_{I}$ or $V_{O}$ = 0 V to 3.6 V; $V_{CC}$ = 0 V	-	-	±0.2	μA
∆I <sub>OFF</sub>	additional power-off leakage current	$V_1$ or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.2	μA
lcc	supply current	$\label{eq:VI} \begin{array}{l} V_I = GND \text{ or } V_{CC}; \ I_O = 0 \ A; \\ V_{CC} = 0.8 \ V \ to \ 3.6 \ V \end{array}$	-	-	0.5	μA
Δl <sub>CC</sub>	additional supply current		<u>[1]</u> -	-	40	μA
CI	input capacitance	$V_{CC}$ = 0 V to 3.6 V; $V_{I}$ = GND or $V_{CC}$	-	0.6	-	pF
Co	output capacitance	$V_{O} = GND; V_{CC} = 0 V$	-	1.3	-	pF

### Low-power dual 2-input AND gate

	Parameter	; voltages are referenced to GND (groun Conditions	Min	Tup	Max	Unit
-		Conditions	IVIITI	Тур	Max	Unit
	40 °C to +85 °C	V 0.8.V	0.70)/			V
VIH	HIGH-level input voltage	$\frac{V_{CC} = 0.8 \text{ V}}{V_{CC} = 0.8 \text{ V}}$	0.70 × V <sub>CC</sub>		-	V
		$V_{CC} = 0.9 \text{ V to } 1.95 \text{ V}$	$0.65 \times V_{CC}$	-	-	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.0	-	-	V
V <sub>IL</sub>	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.30 \times V_{CC}$	
		V <sub>CC</sub> = 0.9 V to 1.95 V	-	-	$0.35 \times V_{CC}$	
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	-	0.9	V
V <sub>ОН</sub>	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_O$ = –20 $\mu A;V_{CC}$ = 0.8 V to 3.6 V	$V_{CC} - 0.1$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.7\times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.03	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.30	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.97	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.85	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.67	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.55	-	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_O$ = 20 $\mu$ A; $V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	$0.3\times V_{CC}$	V
		I <sub>O</sub> = 1.7 mA; V <sub>CC</sub> = 1.4 V	-	-	0.37	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.35	V
		$I_{O} = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.33	V
		I <sub>O</sub> = 3.1 mA; V <sub>CC</sub> = 2.3 V	-	-	0.45	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.45	V
l	input leakage current	$V_{I} = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.5	μA
I <sub>OFF</sub>	power-off leakage current	$V_{\rm I}$ or $V_{\rm O} = 0$ V to 3.6 V; $V_{\rm CC} = 0$ V	-	-	±0.5	μΑ
Δl <sub>OFF</sub>	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.6	μ <b>Α</b>
сс	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.9	μA
Δl <sub>CC</sub>	additional supply current		[1] -	-	50	μA

#### Table 7. Static characteristics ... continued

.... 

### Low-power dual 2-input AND gate

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	40 °C to +125 °C					
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 0.8 V	$0.75 \times V_{CC}$	-	-	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	$0.70 \times V_{CC}$	-	-	V
		$V_{CC} = 2.3 \text{ V} \text{ to } 2.7 \text{ V}$	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	-	-	V
V <sub>IL</sub>	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.25 \times V_{CC}$	V
		$V_{CC} = 0.9 \text{ V} \text{ to } 1.95 \text{ V}$	-	-	$0.30\times V_{CC}$	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
V <sub>OH</sub>	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O}$ = –20 $\mu A;$ $V_{CC}$ = 0.8 V to 3.6 V	$V_{CC}-0.11$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.6 \times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	0.93	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.17	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.77	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.67	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.40	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.30	-	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_O$ = 20 $\mu A; V_{CC}$ = 0.8 V to 3.6 V	-	-	0.11	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	$0.33 \times V_{CC}$	V
		I <sub>O</sub> = 1.7 mA; V <sub>CC</sub> = 1.4 V	-	-	0.41	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.39	V
		$I_{O}$ = 2.3 mA; $V_{CC}$ = 2.3 V	-	-	0.36	V
		$I_{O} = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.50	V
I	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.75	μA
OFF	power-off leakage current	$V_{I}$ or $V_{O}$ = 0 V to 3.6 V; $V_{CC}$ = 0 V	-	-	±0.75	μA
∆I <sub>OFF</sub>	additional power-off leakage current		-	-	±0.75	μA
CC	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; \ I_{O} = 0 \ A; \\ V_{CC} = 0.8 \ V \ to \ 3.6 \ V \end{array}$	-	-	1.4	μA
∆I <sub>CC</sub>	additional supply current		[1] -	-	75	μA

#### Static characteristics ... continued Table 7.

[1] One input at  $V_{CC}$  – 0.6 V, other input at  $V_{CC}$  or GND.

## 11. Dynamic characteristics

#### **Dynamic characteristics** Table 8.

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions		Ta	<sub>mb</sub> = 25 °	C	T <sub>amb</sub> =	-40 °C to	o +125 ℃	Unit
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C <sub>L</sub> = 5 p	ρF									
pd	propagation delay	nA or nB to nY; see Figure 8	[2]							
		$V_{CC} = 0.8 V$		-	17.0	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V		2.6	5.1	10.8	2.1	11.7	12.9	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$		1.6	3.7	6.5	1.5	7.5	8.3	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V		1.3	3.0	5.2	1.3	6.1	6.7	ns
		$V_{CC}$ = 2.3 V to 2.7 V		1.1	2.4	4.0	1.0	4.8	5.3	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		1.0	2.2	3.5	0.9	4.3	4.8	ns
C <sub>L</sub> = 10	pF									
pd	propagation delay	nA or nB to nY; see Figure 8	[2]							
		$V_{CC} = 0.8 V$		-	20.6	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V		2.4	6.0	12.5	2.2	13.6	15.0	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$		2.0	4.3	7.6	1.8	8.9	9.8	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V		1.7	3.6	6.1	1.6	7.2	7.9	ns
		$V_{CC}$ = 2.3 V to 2.7 V		1.4	2.9	4.8	1.3	5.7	6.3	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		1.3	2.7	4.2	1.2	4.7	5.2	ns
C <sub>L</sub> = 15	pF									
pd	propagation delay	nA or nB to nY; see Figure 8	[2]							
		$V_{CC} = 0.8 V$		-	24.1	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V		3.4	6.8	14.2	3.1	15.7	17.3	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V		2.3	4.9	8.6	2.1	10.1	11.2	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V		1.9	4.0	6.9	1.8	8.2	9.0	ns
		$V_{CC}$ = 2.3 V to 2.7 V		1.7	3.4	5.5	1.6	6.5	7.2	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		1.5	3.1	4.8	1.5	5.9	6.5	ns
C <sub>L</sub> = 30	pF									
od	propagation delay	nA or nB to nY; see Figure 8	[2]							
		$V_{CC} = 0.8 V$		-	34.4	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V		4.6	9.1	19.4	4.1	21.8	24.0	ns
		$V_{CC} = 1.4 \text{ V}$ to 1.6 V		3.4	6.4	11.5	2.9	13.6	15.0	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V		2.6	5.3	9.1	2.4	10.9	12.1	ns
		$V_{CC}$ = 2.3 V to 2.7 V		2.3	4.5	7.2	2.2	8.6	9.5	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V		2.2	4.2	6.2	2.1	7.5	8.3	ns

#### Low-power dual 2-input AND gate

Symbol	Parameter	Conditions	Ta	T <sub>amb</sub> = 25 °C			= -40 °C to	) +125 °C	Unit
				Typ <mark>[1]</mark>	Мах	Min	Max (85 °C)	Max (125 °C)	
C <sub>L</sub> = 5 p	F, 10 pF, 15 pF and	30 pF							
C <sub>PD</sub> power dissipation	power dissipation	$f_i = 1 \text{ MHz}; V_I = \text{GND to } V_{\text{CC}}$	L						
	capacitance	$V_{CC} = 0.8 V$	-	2.5	-	-	-	-	pF
		V <sub>CC</sub> = 1.1 V to 1.3 V	-	2.6	-	-	-	-	pF
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	-	2.7	-	-	-	-	pF
		V <sub>CC</sub> = 1.65 V to 1.95 V	-	2.8	-	-	-	-	pF
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	3.2	-	-	-	-	pF
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	3.7	-	-	-	-	pF

#### Dynamic characteristics ... continued Table 8.

[1] All typical values are measured at nominal V<sub>CC</sub>.

#### [2] $t_{pd}$ is the same as $t_{PLH}$ and $t_{PHL}$ .

[3]  $C_{PD}$  is used to determine the dynamic power dissipation (P<sub>D</sub> in  $\mu$ W).

 $P_{D} = C_{PD} \times V_{CC}{}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}{}^2 \times f_o)$  where:

 $f_i$  = input frequency in MHz;

 $f_o = output frequency in MHz;$ 

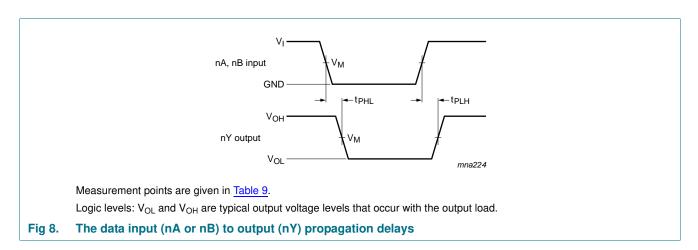
 $C_L$  = output load capacitance in pF;

V<sub>CC</sub> = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_0)$  = sum of the outputs.

### 12. Waveforms

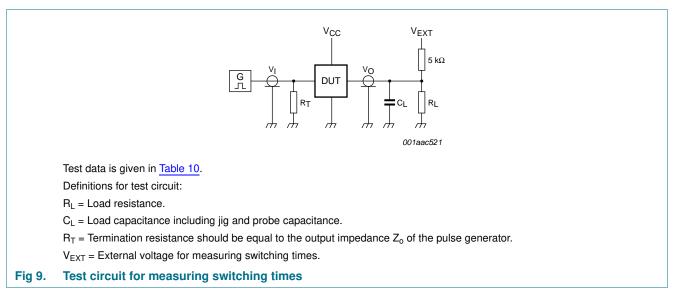


#### Table 9. **Measurement points**

Supply voltage	Output	Input		
V <sub>cc</sub>	V <sub>M</sub>	V <sub>M</sub>	V <sub>I</sub>	t <sub>r</sub> = t <sub>f</sub>
0.8 V to 3.6 V	$0.5  imes V_{CC}$	$0.5\times V_{CC}$	V <sub>CC</sub>	$\leq$ 3.0 ns

74AUP2G08 **Product data sheet** 

#### Low-power dual 2-input AND gate



#### Table 10. Test data

Supply voltage	Load		V <sub>EXT</sub>		
V <sub>cc</sub>	CL	R <sub>L</sub> [1]	t <sub>PLH</sub> , t <sub>PHL</sub>	t <sub>PZH</sub> , t <sub>PHZ</sub>	t <sub>PZL</sub> , t <sub>PLZ</sub>
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k $\Omega$ or 1 M $\Omega$	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times,  $R_L = 5 k\Omega$ .

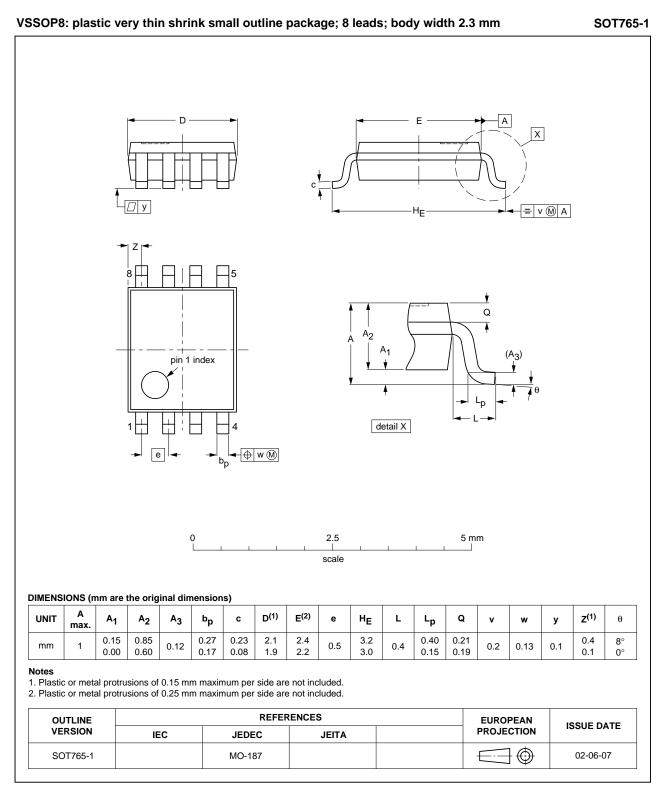
For measuring propagation delays, set-up and hold times and pulse width,  $R_L$  = 1 M $\Omega$ .

### **NXP Semiconductors**

# 74AUP2G08

Low-power dual 2-input AND gate

### 13. Package outline



#### Fig 10. Package outline SOT765-1 (VSSOP8)

All information provided in this document is subject to legal disclaimers.

Low-power dual 2-input AND gate

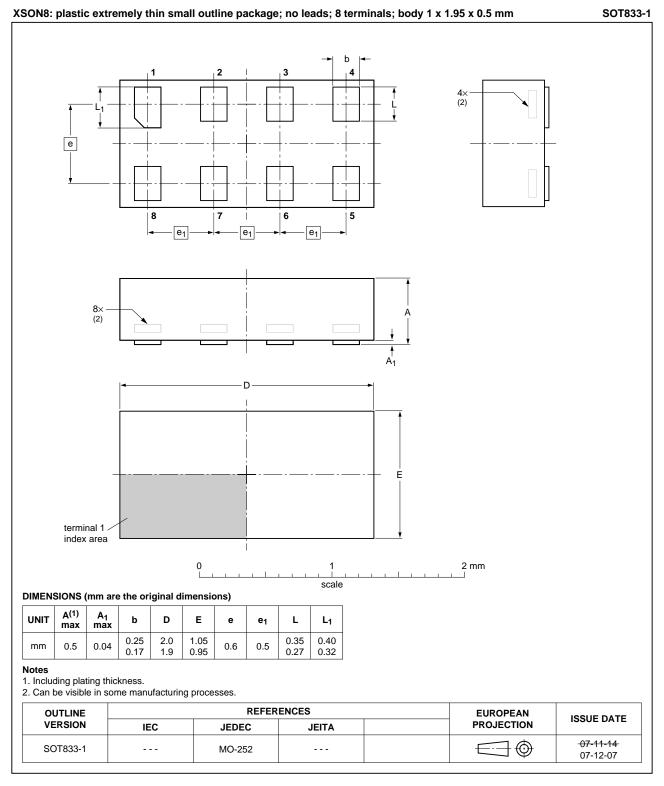
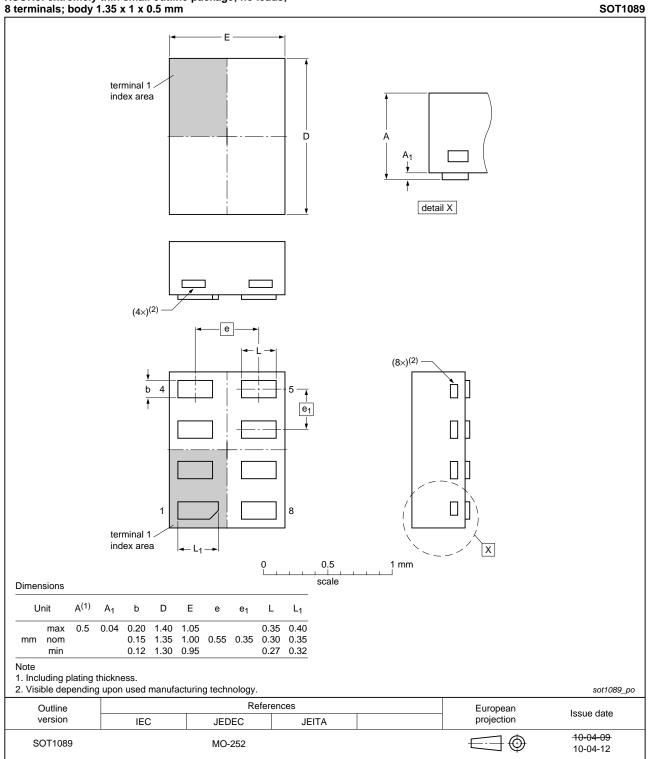


Fig 11. Package outline SOT833-1 (XSON8)

All information provided in this document is subject to legal disclaimers.

Low-power dual 2-input AND gate

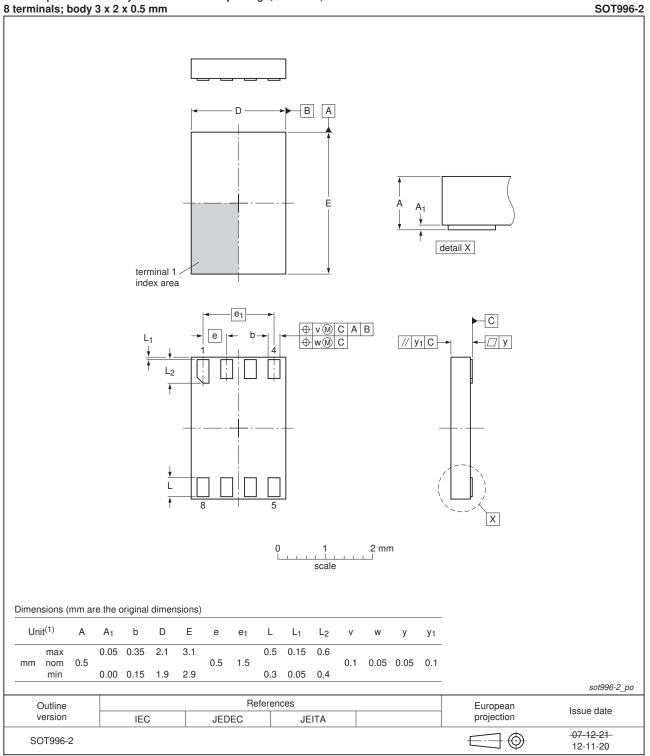


XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.35 x 1 x 0.5 mm

Fig 12. Package outline SOT1089 (XSON8)

All information provided in this document is subject to legal disclaimers.

Low-power dual 2-input AND gate

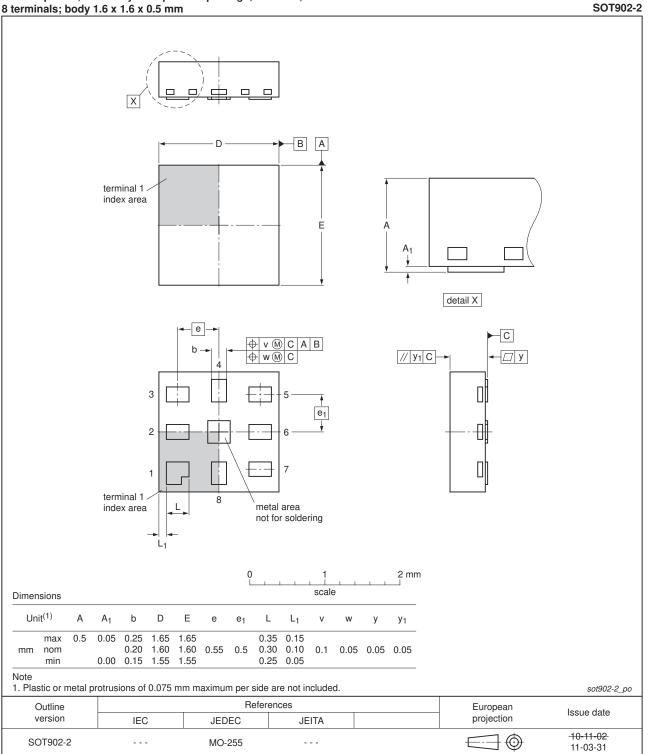


XSON8: plastic extremely thin small outline package; no leads;

Fig 13. Package outline SOT996-2 (XSON8)

All information provided in this document is subject to legal disclaimers.

Low-power dual 2-input AND gate

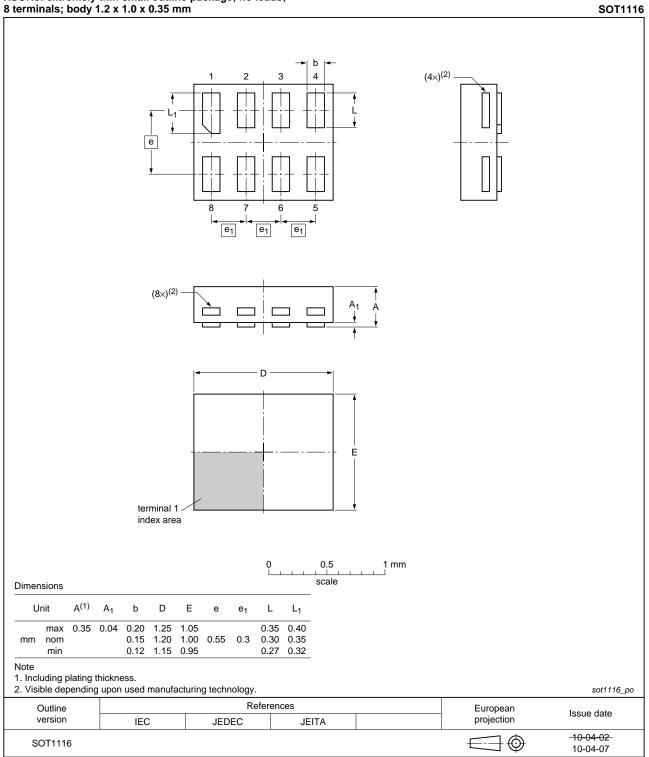


XQFN8: plastic, extremely thin quad flat package; no leads; 8 terminals; body 1.6 x 1.6 x 0.5 mm

#### Fig 14. Package outline SOT902-2 (XQFN8)

All information provided in this document is subject to legal disclaimers.

Low-power dual 2-input AND gate

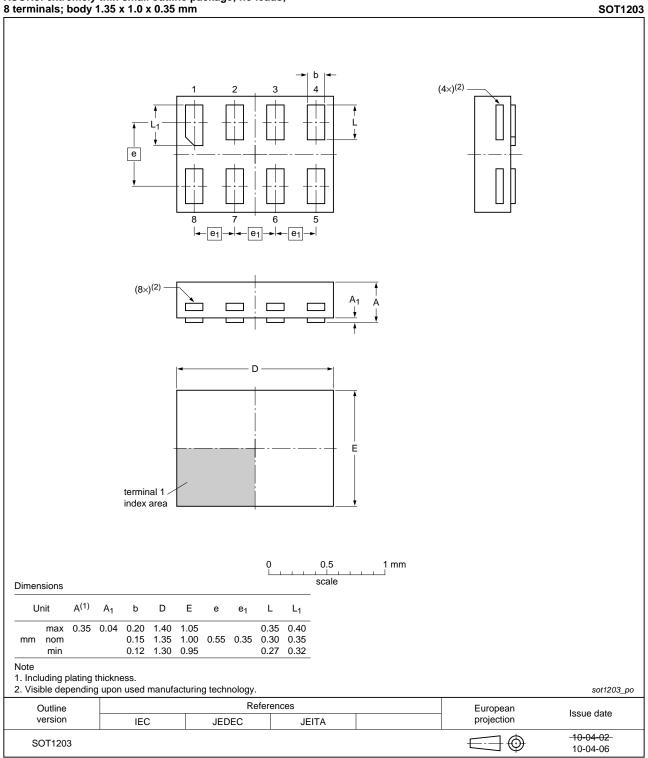


# XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.2 x 1.0 x 0.35 mm

Fig 15. Package outline SOT1116 (XSON8)

All information provided in this document is subject to legal disclaimers.

Low-power dual 2-input AND gate



# XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.35 x 1.0 x 0.35 mm

Fig 16. Package outline SOT1203 (XSON8)

All information provided in this document is subject to legal disclaimers.

Low-power dual 2-input AND gate

## 14. Abbreviations

Table 11. Abbreviations		
Description		
Charged Device Model		
Device Under Test		
ElectroStatic Discharge		
Human Body Model		
Machine Model		
k	Description   Charged Device Model   Device Under Test   ElectroStatic Discharge   Human Body Model	

## **15. Revision history**

Document ID   Release     74AUP2G08 v.7   20130118     Modifications:   • For ty     74AUP2G08 v.6   20120607     74AUP2G08 v.5   20111201	Table 12. Revision history						
Modifications:   • For ty     74AUP2G08 v.6   20120607	date Data sheet status	Change notice	Supersedes				
74AUP2G08 v.6 20120607	Product data sheet	-	74AUP2G08 v.6				
	pe number 74AUP2G08GD XSON	8U has changed to XSON8.					
74ALIP2G08 v 5 20111201	Product data sheet	-	74AUP2G08 v.5				
	Product data sheet	-	74AUP2G08 v.4				
74AUP2G08 v.4 20101109	Product data sheet	-	74AUP2G08 v.3				
74AUP2G08 v.3 20080529	Product data sheet	-	74AUP2G08 v.2				
74AUP2G08 v.2 20080407	Product data sheet	-	74AUP2G08 v.1				
74AUP2G08 v.1 20061006	Product data sheet	-	-				

18 of 21

### 16. Legal information

### 16.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

### 16.2 Definitions

**Draft** — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

**Product specification** — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

### 16.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. NXP Semiconductors takes no responsibility for the content in this document if provided by an information source outside of NXP Semiconductors.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of NXP Semiconductors.

**Right to make changes** — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors and its suppliers accept no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

**Applications** — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using NXP Semiconductors products, and NXP Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the NXP Semiconductors product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using NXP Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). NXP does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at <a href="http://www.nxp.com/profile/terms">http://www.nxp.com/profile/terms</a>, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

**No offer to sell or license** — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

© NXP B.V. 2013. All rights reserved.

#### Low-power dual 2-input AND gate

**Export control** — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

**Non-automotive qualified products** — Unless this data sheet expressly states that this specific NXP Semiconductors product is automotive qualified, the product is not suitable for automotive use. It is neither qualified nor tested in accordance with automotive testing or application requirements. NXP Semiconductors accepts no liability for inclusion and/or use of non-automotive qualified products in automotive equipment or applications.

In the event that customer uses the product for design-in and use in automotive applications to automotive specifications and standards, customer (a) shall use the product without NXP Semiconductors' warranty of the product for such automotive applications, use and specifications, and (b) whenever customer uses the product for automotive applications beyond

NXP Semiconductors' specifications such use shall be solely at customer's own risk, and (c) customer fully indemnifies NXP Semiconductors for any liability, damages or failed product claims resulting from customer design and use of the product for automotive applications beyond NXP Semiconductors' standard warranty and NXP Semiconductors' product specifications.

**Translations** — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

### 16.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

### 17. Contact information

For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: salesaddresses@nxp.com

#### Low-power dual 2-input AND gate

### **18. Contents**

1	General description 1
2	Features and benefits 1
3	Ordering information 2
4	Marking
5	Functional diagram 2
6	Pinning information 3
6.1	Pinning 3
6.2	Pin description 3
7	Functional description 4
8	Limiting values 4
9	Recommended operating conditions 4
10	Static characteristics 5
11	Dynamic characteristics 8
12	Waveforms
13	Package outline 11
14	Abbreviations 18
15	Revision history 18
16	Legal information 19
16.1	Data sheet status 19
16.2	Definitions
16.3	Disclaimers
16.4	Trademarks 20
17	Contact information 20
18	Contents 21

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

#### © NXP B.V. 2013.

All rights reserved.

For more information, please visit: http://www.nxp.com For sales office addresses, please send an email to: salesaddresses@nxp.com

Date of release: 18 January 2013 Document identifier: 74AUP2G08